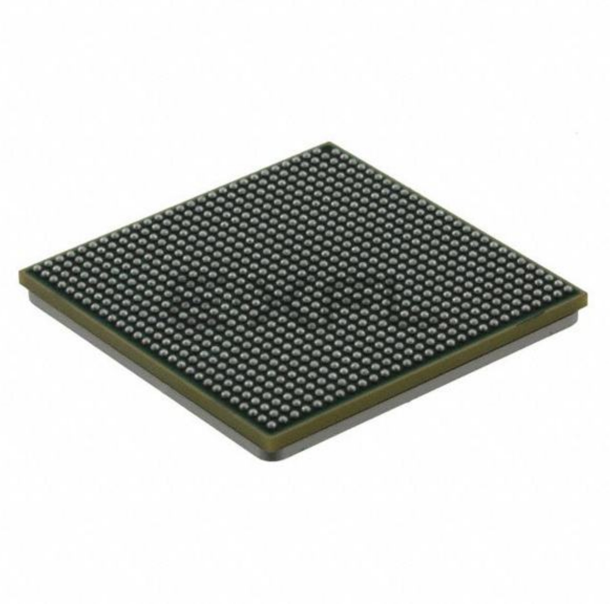

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Understanding Embedded - Microprocessors

Embedded microprocessors are specialized computing chips designed to perform specific tasks within an embedded system. Unlike general-purpose microprocessors found in personal computers, embedded microprocessors are tailored for dedicated functions within larger systems, offering optimized performance, efficiency, and reliability. These microprocessors are integral to the operation of countless electronic devices, providing the computational power necessary for controlling processes, handling data, and managing communications.

Applications of Embedded - Microprocessors

Embedded microprocessors are utilized across a broad spectrum of applications, making them indispensable in

Details	
Product Status	Obsolete
Core Processor	PowerPC e500
Number of Cores/Bus Width	1 Core, 32-Bit
Speed	1.0GHz
Co-Processors/DSP	Security; SEC
RAM Controllers	DDR, SDRAM
Graphics Acceleration	No
Display & Interface Controllers	-
Ethernet	10/100/1000Mbps (2)
SATA	-
USB	-
Voltage - I/O	2.5V, 3.3V
Operating Temperature	0°C ~ 105°C (TA)
Security Features	Cryptography, Random Number Generator
Package / Case	783-BBGA, FCBGA
Supplier Device Package	783-FCPBGA (29x29)
Purchase URL	https://www.e-xfl.com/product-detail/nxp-semiconductors/kmpc8541evtaqf

- Four global high resolution timers/counters that can generate interrupts
- Supports additional internal interrupt sources
- Supports fully nested interrupt delivery
- Interrupts can be routed to external pin for external processing
- Interrupts can be routed to the e500 core's standard or critical interrupt inputs
- Interrupt summary registers allow fast identification of interrupt source

- Two I^2C controllers (one is contained within the CPM, the other is a stand-alone controller which is not part of the CPM)
  - Two-wire interface
  - Multiple master support
  - Master or slave I^2C mode support
  - On-chip digital filtering rejects spikes on the bus
- Boot sequencer
  - Optionally loads configuration data from serial ROM at reset via the stand-alone I^2C interface
  - Can be used to initialize configuration registers and/or memory
  - Supports extended I^2C addressing mode
  - Data integrity checked with preamble signature and CRC
- DUART
  - Two 4-wire interfaces (RXD, TXD, RTS, CTS)
  - Programming model compatible with the original 16450 UART and the PC16550D
- Local bus controller (LBC)
  - Multiplexed 32-bit address and data operating at up to 166 MHz
  - Eight chip selects support eight external slaves
  - Up to eight-beat burst transfers
  - The 32-, 16-, and 8-bit port sizes are controlled by an on-chip memory controller
  - Three protocol engines available on a per chip select basis:
    - General purpose chip select machine (GPCM)
    - Three user programmable machines (UPMs)
    - Dedicated single data rate SDRAM controller
  - Parity support
  - Default boot ROM chip select with configurable bus width (8-, 16-, or 32-bit)
- Two Three-speed (10/100/1000)Ethernet controllers (TSECs)
  - Dual IEEE 802.3, 802.3u, 802.3x, 802.3z AC compliant controllers
  - Support for Ethernet physical interfaces:
    - 10/100/1000 Mbps IEEE 802.3 GMII
    - 10/100 Mbps IEEE 802.3 MII
    - 10 Mbps IEEE 802.3 MII

2.1.1 Absolute Maximum Ratings

Table 1 provides the absolute maximum ratings.

Table 1. Absolute Maximum Ratings [1]

Characteristic		Symbol	Max Value	Unit	Notes
Core supply voltage		V_{DD}	–0.3 to 1.32 0.3 to 1.43 (for 1 GHz only)	V	
PLL supply voltage		AV_{DD}	–0.3 to 1.32 0.3 to 1.43 (for 1 GHz only)	V	
DDR DRAM I/O voltage		GV_{DD}	–0.3 to 3.63	V	
Three-speed Ethernet I/O, MII management voltage		LV_{DD}	–0.3 to 3.63 –0.3 to 2.75	V	
CPM, PCI, local bus, DUART, system control and power management, I^2C, and JTAG I/O voltage		OV_{DD}	–0.3 to 3.63	V	3
Input voltage	DDR DRAM signals	MV_{IN}	–0.3 to (GV_{DD} + 0.3)	V	2, 5
	DDR DRAM reference	MV_{REF}	–0.3 to (GV_{DD} + 0.3)	V	2, 5
	Three-speed Ethernet signals	LV_{IN}	–0.3 to (LV_{DD} + 0.3)	V	4, 5
	CPM, Local bus, DUART, SYSCLK, system control and power management, I^2C, and JTAG signals	OV_{IN}	–0.3 to (OV_{DD} + 0.3)1	V	5
	PCI	OV_{IN}	–0.3 to (OV_{DD} + 0.3)	V	6
Storage temperature range		T_{STG}	–55 to 150	°C	

Notes:
1. Functional and tested operating conditions are given in Table 2. Absolute maximum ratings are stress ratings only, and functional operation at the maximums is not guaranteed. Stresses beyond those listed may affect device reliability or cause permanent damage to the device.
2. **Caution:** MV_{IN} must not exceed GV_{DD} by more than 0.3 V. This limit may be exceeded for a maximum of 20 ms during power-on reset and power-down sequences.
3. **Caution:** OV_{IN} must not exceed OV_{DD} by more than 0.3 V. This limit may be exceeded for a maximum of 20 ms during power-on reset and power-down sequences.
4. **Caution:** LV_{IN} must not exceed LV_{DD} by more than 0.3 V. This limit may be exceeded for a maximum of 20 ms during power-on reset and power-down sequences.
5. (M,L,O)V_{IN} and MV_{REF} may overshoot/undershoot to a voltage and for a maximum duration as shown in Figure 2.
6. OV_{IN} on the PCI interface may overshoot/undershoot according to the PCI Electrical Specification for 3.3-V operation, as shown in Figure 3.

2.1.2 Power Sequencing

The MPC8541Erequires its power rails to be applied in a specific sequence in order to ensure proper device operation. These requirements are as follows for power up:

1. V_{DD}, AV_{DDn}
2. GV_{DD}, LV_{DD}, OV_{DD} (I/O supplies)

Items on the same line have no ordering requirement with respect to one another. Items on separate lines must be ordered sequentially such that voltage rails on a previous step must reach 90 percent of their value before the voltage rails on the current step reach ten percent of theirs.

NOTE

If the items on line 2 must precede items on line 1, please ensure that the delay does not exceed 500 ms and the power sequence is not done greater than once per day in production environment.

NOTE

From a system standpoint, if the I/O power supplies ramp prior to the V_{DD} core supply, the I/Os on the MPC8541E may drive a logic one or zero during power-up.

2.1.3 Recommended Operating Conditions

Table 2 provides the recommended operating conditions for the MPC8541E. Note that the values in Table 2 are the recommended and tested operating conditions. Proper device operation outside of these conditions is not guaranteed.

Table 2. Recommended Operating Conditions

Characteristic		Symbol	Recommended Value	Unit
Core supply voltage		V_{DD}	1.2 V ± 60 mV 1.3 V± 50 mV (for 1 GHz only)	V
PLL supply voltage		AV_{DD}	1.2 V ± 60 mV 1.3 V ± 50 mV (for 1 GHz only)	V
DDR DRAM I/O voltage		GV_{DD}	2.5 V ± 125 mV	V
Three-speed Ethernet I/O voltage		LV_{DD}	3.3 V ± 165 mV 2.5 V ± 125 mV	V
PCI, local bus, DUART, system control and power management, I^{2}C, and JTAG I/O voltage		OV_{DD}	3.3 V ± 165 mV	V
Input voltage	DDR DRAM signals	MV_{IN}	GND to GV_{DD}	V
	DDR DRAM reference	MV_{REF}	GND to GV_{DD}	V
	Three-speed Ethernet signals	LV_{IN}	GND to LV_{DD}	V
	PCI, local bus, DUART, SYSCLK, system control and power management, I^{2}C, and JTAG signals	OV_{IN}	GND to OV_{DD}	V
Die-junction Temperature		T_j	0 to 105	°C

3 Power Characteristics

The estimated typical power dissipation for this family of PowerQUICC III devices is shown in Table 4.

Table 4. Power Dissipation(1) (2)

CCB Frequency (MHz)	Core Frequency (MHz)	V_{DD}	Typical Power(3)(4) (W)	Maximum Power(5) (W)
200	400	1.2	4.4	6.1
	500	1.2	4.7	6.5
	600	1.2	5.0	6.8
267	533	1.2	4.9	6.7
	667	1.2	5.4	7.2
	800	1.2	5.8	8.6
333	667	1.2	5.5	7.4
	833	1.2	6.0	8.8
	1000(6)	1.3	9.0	12.2

Notes:

1. The values do not include I/O supply power (OV_{DD}, LV_{DD}, GV_{DD}) or AV_{DD}.
2. Junction temperature is a function of die size, on-chip power dissipation, package thermal resistance, mounting site (board) temperature, ambient temperature, air flow, power dissipation of other components on the board, and board thermal resistance. Any customer design must take these considerations into account to ensure the maximum 105 degrees junction temperature is not exceeded on this device.
3. Typical power is based on a nominal voltage of V_{DD} = 1.2V, a nominal process, a junction temperature of T_j = 105° C, and a Dhrystone 2.1 benchmark application.
4. Thermal solutions likely need to design to a value higher than Typical Power based on the end application, T_A target, and I/O power
5. Maximum power is based on a nominal voltage of V_{DD} = 1.2V, worst case process, a junction temperature of T_j = 105° C, and an artificial smoke test.
6. The nominal recommended V_{DD} = 1.3V for this speed grade.

Notes:

1.

2.

3.

4.

5.

6.

4.3 Real Time Clock Timing

Table 8 provides the real time clock (RTC) AC timing specifications.

Table 8. RTC AC Timing Specifications

Parameter/Condition	Symbol	Min	Typical	Max	Unit	Notes
RTC clock high time	t_{RTCH}	2 x t_{CCB_CLK}	—	—	ns	—
RTC clock low time	t_{RTCL}	2 x t_{CCB_CLK}	—	—	ns	—

5 RESET Initialization

This section describes the AC electrical specifications for the RESET initialization timing requirements of the MPC8541E. Table 9 provides the RESET initialization AC timing specifications.

Table 9. RESET Initialization Timing Specifications

Parameter/Condition	Min	Max	Unit	Notes
Required assertion time of $\overline{\text{HRESET}}$	100	—	µs	—
Minimum assertion time for $\overline{\text{SRESET}}$	512	—	SYSCLKs	1
PLL input setup time with stable SYSCLK before HRESET negation	100	—	µs	—
Input setup time for POR configs (other than PLL config) with respect to negation of $\overline{\text{HRESET}}$	4	—	SYSCLKs	1
Input hold time for POR configs (including PLL config) with respect to negation of $\overline{\text{HRESET}}$	2	—	SYSCLKs	1
Maximum valid-to-high impedance time for actively driven POR configs with respect to negation of $\overline{\text{HRESET}}$	—	5	SYSCLKs	1

Notes:
1. SYSCLK is identical to the PCI_CLK signal and is the primary clock input for the MPC8541E. See the *MPC8555E PowerQUICC™ III Integrated Communications Processor Reference Manual* for more details.

Table 10 provides the PLL and DLL lock times.

Table 10. PLL and DLL Lock Times

Parameter/Condition	Min	Max	Unit	Notes
PLL lock times	—	100	µs	—
DLL lock times	7680	122,880	CCB Clocks	1, 2

Notes:
1. DLL lock times are a function of the ratio between the output clock and the platform (or CCB) clock. A 2:1 ratio results in the minimum and an 8:1 ratio results in the maximum.
2. The CCB clock is determined by the SYSCLK × platform PLL ratio.

Figure 6 provides the AC test load for the DDR bus.

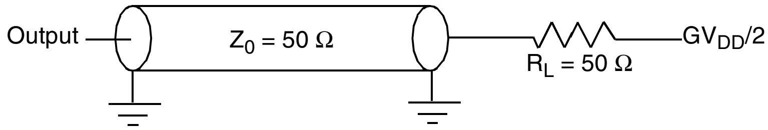


Figure 6. DDR AC Test Load

Table 15. DDR SDRAM Measurement Conditions

Symbol	DDR	Unit	Notes
V_{TH}	$MV_{REF} \pm 0.31$ V	V	1
V_{OUT}	$0.5 \times GV_{DD}$	V	2

Notes:
1. Data input threshold measurement point.
2. Data output measurement point.

7 DUART

This section describes the DC and AC electrical specifications for the DUART interface of the MPC8541E.

7.1 DUART DC Electrical Characteristics

Table 16 provides the DC electrical characteristics for the DUART interface of the MPC8541E.

Table 16. DUART DC Electrical Characteristics

Parameter	Symbol	Test Condition	Min	Max	Unit
High-level input voltage	V_{IH}	$V_{OUT} \geq V_{OH}$ (min) or	2	$OV_{DD} + 0.3$	V
Low-level input voltage	V_{IL}	$V_{OUT} \leq V_{OL}$ (max)	–0.3	0.8	V
Input current	I_{IN}	V_{IN} [1] = 0 V or $V_{IN} = V_{DD}$	—	±5	μA
High-level output voltage	V_{OH}	OV_{DD} = min, $I_{OH} = -100$ μA	$OV_{DD} - 0.2$	—	V
Low-level output voltage	V_{OL}	OV_{DD} = min, I_{OL} = 100 μA	—	0.2	V

Note:
1. Note that the symbol V_{IN}, in this case, represents the OV_{IN} symbol referenced in Table 1 and Table 2.

Figure 14 shows the RBMII and RTBI AC timing and multiplexing diagrams.

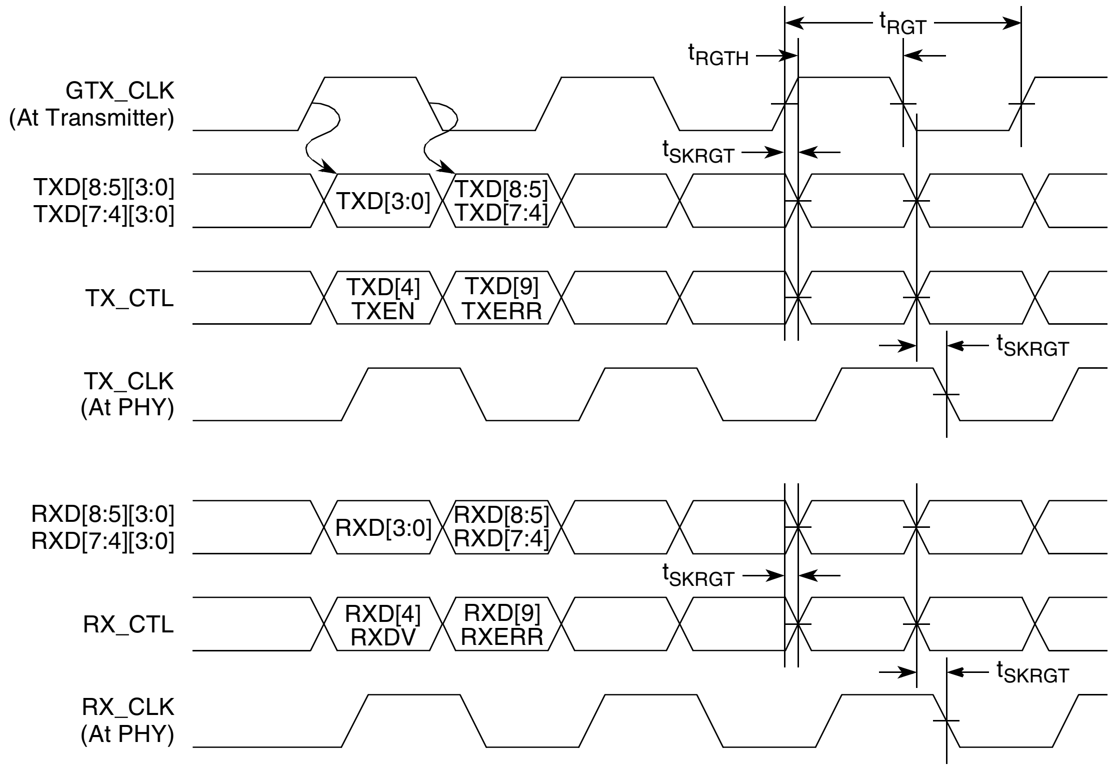


Figure 14. RGMII and RTBI AC Timing and Multiplexing Diagrams

8.3 Ethernet Management Interface Electrical Characteristics

The electrical characteristics specified here apply to MII management interface signals MDIO (management data input/output) and MDC (management data clock). The electrical characteristics for GMII, RGMII, TBI and RTBI are specified in Section 8.1, "Three-Speed Ethernet Controller (TSEC) (10/100/1000 Mbps)—GMII/MII/TBI/RGMII/RTBI Electrical Characteristics."

8.3.1 MII Management DC Electrical Characteristics

The MDC and MDIO are defined to operate at a supply voltage of 3.3 V. The DC electrical characteristics for MDIO and MDC are provided in Table 27.

Table 27. MII Management DC Electrical Characteristics

Parameter	Symbol	Conditions		Min	Max	Unit
Supply voltage (3.3 V)	OV_{DD}	—		3.13	3.47	V
Output high voltage	V_{OH}	I_{OH} = –1.0 mA	LV_{DD} = Min	2.10	LV_{DD} + 0.3	V
Output low voltage	V_{OL}	I_{OL} = 1.0 mA	LV_{DD} = Min	GND	0.50	V
Input high voltage	V_{IH}	—		1.70	—	V
Input low voltage	V_{IL}	—		—	0.90	V

Table 30. Local Bus General Timing Parameters—DLL Enabled (continued)

Parameter	Configuration [7]	Symbol [1]	Min	Max	Unit	Notes
Local bus clock to output high impedance for LAD/LDP	$\overline{\text{LWE}}$[0:1] = 00	$t_{LBKHOZ2}$	—	2.8	ns	5, 9
	$\overline{\text{LWE}}$[0:1] = 11 (default)			4.2		

Notes:
1. The symbols used for timing specifications herein follow the pattern of $t_{\text{(First two letters of functional block)(signal)(state)(reference)(state)}}$ for inputs and $t_{\text{(First two letters of functional block)(reference)(state)(signal)(state)}}$ for outputs. For example, $t_{LBIXKH1}$ symbolizes local bus timing (LB) for the input (I) to go invalid (X) with respect to the time the t_{LBK} clock reference (K) goes high (H), in this case for clock one(1). Also, t_{LBKHOX} symbolizes local bus timing (LB) for the t_{LBK} clock reference (K) to go high (H), with respect to the output (O) going invalid (X) or output hold time.
2. All timings are in reference to LSYNC_IN for DLL enabled mode.
3. All signals are measured from $OV_{DD}/2$ of the rising edge of LSYNC_IN for DLL enabled to $0.4 \times OV_{DD}$ of the signal in question for 3.3-V signaling levels.
4. Input timings are measured at the pin.
5. For purposes of active/float timing measurements, the Hi-Z or off state is defined to be when the total current delivered through the component pin is less than or equal to the leakage current specification.
6. The value of t_{LBOTOT} is defined as the sum of 1/2 or 1 ccb_clk cycle as programmed by LBCR[AHD], and the number of local bus buffer delays used as programmed at power-on reset with configuration pins $\overline{\text{LWE}}$[0:1].
7. Maximum possible clock skew between a clock LCLK[m] and a relative clock LCLK[n]. Skew measured between complementary signals at $OV_{DD}/2$.
8. Guaranteed by characterization.
9. Guaranteed by design.

Table 31 describes the general timing parameters of the local bus interface of the MPC8541E with the DLL bypassed.

Table 31. Local Bus General Timing Parameters—DLL Bypassed

Parameter	Configuration [7]	Symbol [1]	Min	Max	Unit	Notes
Local bus cycle time	—	t_{LBK}	6.0	—	ns	2
Internal launch/capture clock to LCLK delay	—	t_{LBKHKT}	1.8	3.4	ns	8
LCLK[n] skew to LCLK[m] or LSYNC_OUT	—	$t_{LBKSKEW}$	—	150	ps	7, 9
Input setup to local bus clock (except LUPWAIT)	—	$t_{LBIVKH1}$	5.2	—	ns	3, 4
LUPWAIT input setup to local bus clock	—	$t_{LBIVKH2}$	5.1	—	ns	3, 4
Input hold from local bus clock (except LUPWAIT)	—	$t_{LBIXKH1}$	–1.3	—	ns	3, 4
LUPWAIT input hold from local bus clock	—	$t_{LBIXKH2}$	–0.8	—	ns	3, 4
LALE output transition to LAD/LDP output transition (LATCH hold time)	—	t_{LBOTOT}	1.5	—	ns	6
Local bus clock to output valid (except LAD/LDP and LALE)	$\overline{\text{LWE}}$[0:1] = 00	$t_{LBKLOV1}$	—	0.5	ns	3
	$\overline{\text{LWE}}$[0:1] = 11 (default)			2.0		
Local bus clock to data valid for LAD/LDP	$\overline{\text{LWE}}$[0:1] = 00	$t_{LBKLOV2}$	—	0.7	ns	3
	$\overline{\text{LWE}}$[0:1] = 11 (default)			2.2		

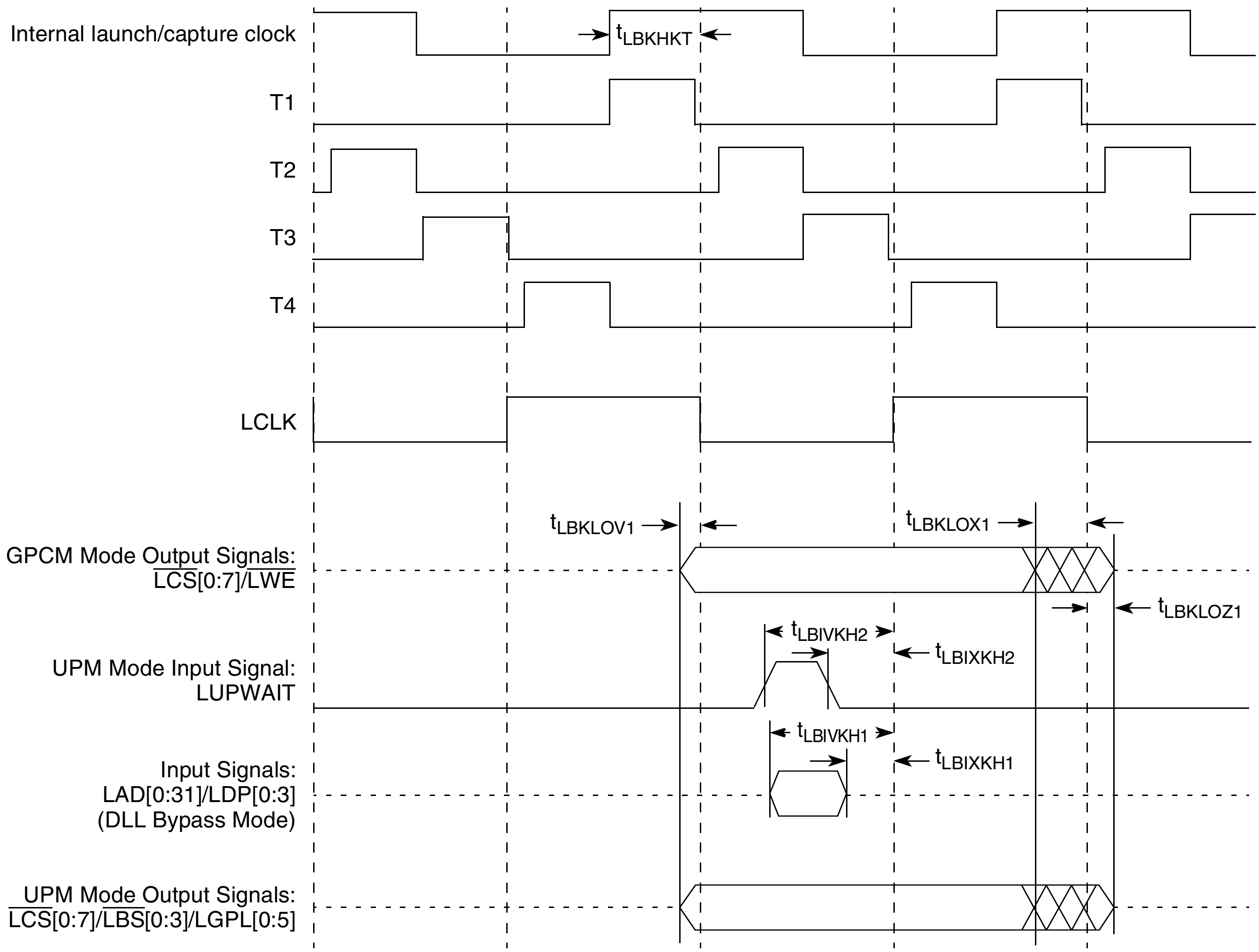


Figure 22. Local Bus Signals, GPCM/UPM Signals for LCCR[CLKDIV] = 4 or 8 (DLL Bypass Mode)

Table 33. CPM Input AC Timing Specifications [1] (continued)

Characteristic	Symbol [2]	Min[3]	Unit
PIO inputs—input hold time	t_{PIIXKH}	1	ns
COL width high (FCC)	t_{FCCH}	1.5	CLK

Notes:
1. Input specifications are measured from the 50% level of the signal to the 50% level of the rising edge of CLKIN. Timings are measured at the pin.
2. The symbols used for timing specifications herein follow the pattern of $t_{\text{(first two letters of functional block)(signal)(state)(reference)(state)}}$ for inputs and $t_{\text{(first two letters of functional block)(reference)(state)(signal)(state)}}$ for outputs. For example, t_{FIIVKH} symbolizes the FCC inputs internal timing (FI) with respect to the time the input signals (I) reaching the valid state (V) relative to the reference clock t_{FCC} (K) going to the high (H) state or setup time.
3. PIO and TIMER inputs and outputs are asynchronous to SYSCLK or any other externally visible clock. PIO/TIMER inputs are internally synchronized to the CPM internal clock. PIO/TIMER outputs should be treated as asynchronous.

Table 34. CPM Output AC Timing Specifications [1]

Characteristic	Symbol [2]	Min	Max	Unit
FCC outputs—internal clock (NMSI) delay	t_{FIKHOX}	1	5.5	ns
FCC outputs—external clock (NMSI) delay	t_{FEKHOX}	2	8	ns
SPI outputs—internal clock (NMSI) delay	t_{NIKHOX}	0.5	10	ns
SPI outputs—external clock (NMSI) delay	t_{NEKHOX}	2	8	ns
PIO outputs delay	t_{PIKHOX}	1	11	ns

Notes:
1. Output specifications are measured from the 50% level of the rising edge of CLKIN to the 50% level of the signal. Timings are measured at the pin.
2. The symbols used for timing specifications follow the pattern of $t_{\text{(first two letters of functional block)(signal)(state) (reference)(state)}}$ for inputs and $t_{\text{(first two letters of functional block)(reference)(state)(signal)(state)}}$ for outputs. For example, t_{FIKHOX} symbolizes the FCC inputs internal timing (FI) for the time t_{FCC} memory clock reference (K) goes from the high state (H) until outputs (O) are invalid (X).

Figure 23 provides the AC test load for the CPM.

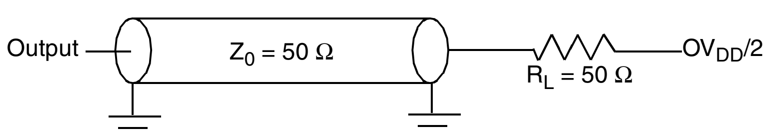


Figure 23. CPM AC Test Load

Figure 35 provides the test access port timing diagram.

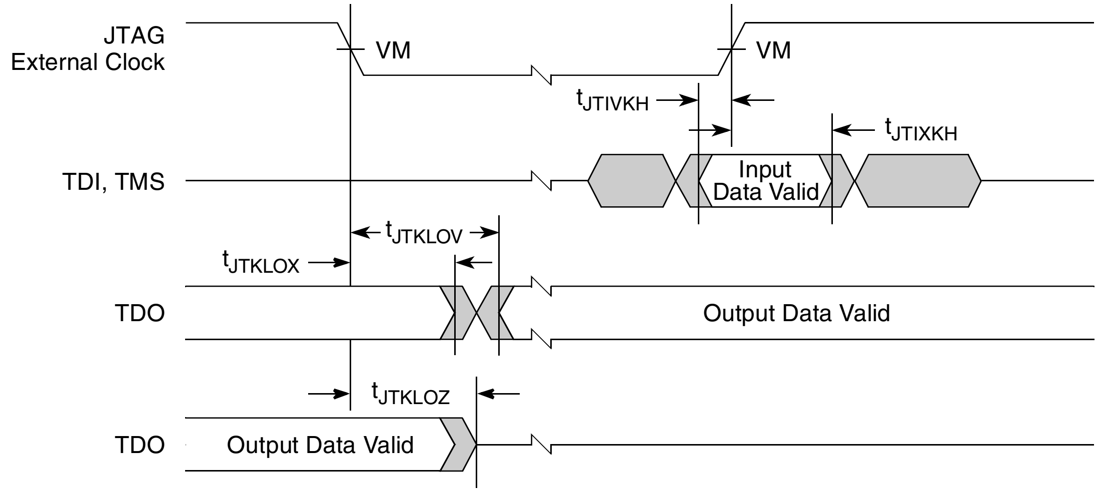


Figure 35. Test Access Port Timing Diagram

12 I^2C

This section describes the DC and AC electrical characteristics for the I^2C interface of the MPC8541E.

12.1 I^2C DC Electrical Characteristics

Table 39 provides the DC electrical characteristics for the I^2C interface of the MPC8541E.

Table 39. I^2C DC Electrical Characteristics

At recommended operating conditions with OV_{DD} of 3.3 V ± 5%.

Parameter	Symbol	Min	Max	Unit	Notes
Input high voltage level	V_{IH}	$0.7 \times OV_{DD}$	OV_{DD}+ 0.3	V	—
Input low voltage level	V_{IL}	–0.3	$0.3 \times OV_{DD}$	V	—
Low level output voltage	V_{OL}	0	$0.2 \times OV_{DD}$	V	1
Output fall time from V_{IH}(min) to V_{IL}(max) with a bus capacitance from 10 to 400 pF	t_{I2KLKV}	$20 + 0.1 \times C_B$	250	ns	2
Pulse width of spikes which must be suppressed by the input filter	t_{I2KHKL}	0	50	ns	3
Input current each I/O pin (input voltage is between $0.1 \times OV_{DD}$ and $0.9 \times OV_{DD}$(max)	I_I	–10	10	μA	4
Capacitance for each I/O pin	C_I	—	10	pF	—

Notes:
1. Output voltage (open drain or open collector) condition = 3 mA sink current.
2. C_B = capacitance of one bus line in pF.
3. Refer to the *MPC8555E PowerQUICC™ III Integrated Communications Processor Reference Manual* for information on the digital filter used.
4. I/O pins obstruct the SDA and SCL lines if OV_{DD} is switched off.

14.3 Pinout Listings

Table 43 provides the pin-out listing for the MPC8541E, 783 FC-PBGA package.

Table 43. MPC8541E Pinout Listing

Signal	Package Pin Number	Pin Type	Power Supply	Notes
PCI1 and PCI2 (one 64-bit or two 32-bit)				
PCI1_AD[63:32], PCI2_AD[31:0]	AA14, AB14, AC14, AD14, AE14, AF14, AG14, AH14, V15, W15, Y15, AA15, AB15, AC15, AD15, AG15, AH15, V16, W16, AB16, AC16, AD16, AE16, AF16, V17, W17, Y17, AA17, AB17, AE17, AF17, AF18	I/O	OV_{DD}	17
PCI1_AD[31:0]	AH6, AD7, AE7, AH7, AB8, AC8, AF8, AG8, AD9, AE9, AF9, AG9, AH9, W10, Y10, AA10, AE11, AF11, AG11, AH11, V12, W12, Y12, AB12, AD12, AE12, AG12, AH12, V13, Y13, AB13, AC13	I/O	OV_{DD}	17
PCI_C_BE64[7:4] PCI2_C_BE[3:0]	AG13, AH13, V14, W14	I/O	OV_{DD}	17
PCI_C_BE64[3:0] PCI1_C_BE[3:0]	AH8, AB10, AD11, AC12	I/O	OV_{DD}	17
PCI1_PAR	AA11	I/O	OV_{DD}	—
PCI1_PAR64/PCI2_PAR	Y14	I/O	OV_{DD}	—
PCI1_FRAME	AC10	I/O	OV_{DD}	2
PCI1_TRDY	AG10	I/O	OV_{DD}	2
PCI1_IRDY	AD10	I/O	OV_{DD}	2
PCI1_STOP	V11	I/O	OV_{DD}	2
PCI1_DEVSEL	AH10	I/O	OV_{DD}	2
PCI1_IDSEL	AA9	I	OV_{DD}	—
PCI1_REQ64/PCI2_FRAME	AE13	I/O	OV_{DD}	5, 10
PCI1_ACK64/PCI2_DEVSEL	AD13	I/O	OV_{DD}	2
PCI1_PERR	W11	I/O	OV_{DD}	2
PCI1_SERR	Y11	I/O	OV_{DD}	2, 4
PCI1_REQ[0]	AF5	I/O	OV_{DD}	—
PCI1_REQ[1:4]	AF3, AE4, AG4, AE5	I	OV_{DD}	—
PCI1_GNT[0]	AE6	I/O	OV_{DD}	—
PCI1_GNT[1:4]	AG5, AH5, AF6, AG6	O	OV_{DD}	5, 9
PCI1_CLK	AH25	I	OV_{DD}	—
PCI2_CLK	AH27	I	OV_{DD}	—
PCI2_GNT[0]	AC18	I/O	OV_{DD}	—

Table 43. MPC8541E Pinout Listing (continued)

Signal	Package Pin Number	Pin Type	Power Supply	Notes
LA[28:31]	T18, T19, T20, T21	O	OV_{DD}	5, 7, 9
LAD[0:31]	AD26, AD27, AD28, AC26, AC27, AC28, AA22, AA23, AA26, Y21, Y22, Y26, W20, W22, W26, V19, T22, R24, R23, R22, R21, R18, P26, P25, P20, P19, P18, N22, N23, N24, N25, N26	I/O	OV_{DD}	—
LALE	V21	O	OV_{DD}	5, 8, 9
LBCTL	V20	O	OV_{DD}	9
LCKE	U23	O	OV_{DD}	—
LCLK[0:2]	U27, U28, V18	O	OV_{DD}	—
$\overline{\text{LCS}}$[0:4]	Y27, Y28, W27, W28, R27	O	OV_{DD}	—
$\overline{\text{LCS5}}$/$\overline{\text{DMA\_DREQ2}}$	R28	I/O	OV_{DD}	1
$\overline{\text{LCS6}}$/$\overline{\text{DMA\_DACK2}}$	P27	O	OV_{DD}	1
$\overline{\text{LCS7}}$/$\overline{\text{DMA\_DDONE2}}$	P28	O	OV_{DD}	1
LDP[0:3]	AA27, AA28, T26, P21	I/O	OV_{DD}	—
LGPL0/LSDA10	U19	O	OV_{DD}	5, 9
LGPL1/$\overline{\text{LSDWE}}$	U22	O	OV_{DD}	5, 9
LGPL2/$\overline{\text{LOE}}$/$\overline{\text{LSDRAS}}$	V28	O	OV_{DD}	5, 8, 9
LGPL3/$\overline{\text{LSDCAS}}$	V27	O	OV_{DD}	5, 9
LGPL4/$\overline{\text{LGTA}}$/LUPWAIT/ LPBSE	V23	I/O	OV_{DD}	21
LGPL5	V22	O	OV_{DD}	5, 9
LSYNC_IN	T27	I	OV_{DD}	—
LSYNC_OUT	T28	O	OV_{DD}	—
$\overline{\text{LWE}}$[0:1]/LSDDQM[0:1]/ $\overline{\text{LBS}}$[0:1]	AB28, AB27	O	OV_{DD}	1, 5, 9
$\overline{\text{LWE}}$[2:3]/LSDDQM[2:3]/ $\overline{\text{LBS}}$[2:3]	T23, P24	O	OV_{DD}	1, 5, 9
DMA				
$\overline{\text{DMA\_DREQ}}$[0:1]	H5, G4	I	OV_{DD}	—
$\overline{\text{DMA\_DACK}}$[0:1]	H6, G5	O	OV_{DD}	—
$\overline{\text{DMA\_DDONE}}$[0:1]	H7, G6	O	OV_{DD}	—
Programmable Interrupt Controller				
$\overline{\text{MCP}}$	AG17	I	OV_{DD}	—
$\overline{\text{UDE}}$	AG16	I	OV_{DD}	—

Table 43. MPC8541E Pinout Listing (continued)

Signal	Package Pin Number	Pin Type	Power Supply	Notes
TSEC2_CRS	D9	I	LV_{DD}	—
TSEC2_COL	F8	I	LV_{DD}	—
TSEC2_RXD[7:0]	F9, E9, C9, B9, A9, H9, G10, F10	I	LV_{DD}	—
TSEC2_RX_DV	H8	I	LV_{DD}	—
TSEC2_RX_ER	A8	I	LV_{DD}	—
TSEC2_RX_CLK	E10	I	LV_{DD}	—
DUART				
$\overline{\text{UART\_CTS}}$[0,1]	Y2, Y3	I	OV_{DD}	—
$\overline{\text{UART\_RTS}}$[0,1]	Y1, AD1	O	OV_{DD}	—
UART_SIN[0,1]	P11, AD5	I	OV_{DD}	—
UART_SOUT[0,1]	N6, AD2	O	OV_{DD}	—
I^2C interface				
IIC_SDA	AH22	I/O	OV_{DD}	4, 19
IIC_SCL	AH23	I/O	OV_{DD}	4, 19
System Control				
$\overline{\text{HRESET}}$	AH16	I	OV_{DD}	—
$\overline{\text{HRESET\_REQ}}$	AG20	O	OV_{DD}	18
$\overline{\text{SRESET}}$	AF20	I	OV_{DD}	—
$\overline{\text{CKSTP\_IN}}$	M11	I	OV_{DD}	—
$\overline{\text{CKSTP\_OUT}}$	G1	O	OV_{DD}	2, 4
Debug				
TRIG_IN	N12	I	OV_{DD}	—
TRIG_OUT/READY	G2	O	OV_{DD}	6, 9, 18
MSRCID[0:1]	J9, G3	O	OV_{DD}	5, 6, 9
MSRCID[2:3]	F3, F5	O	OV_{DD}	6
MSRCID4	F2	O	OV_{DD}	6
MDVAL	F4	O	OV_{DD}	6
Clock				
SYSCLK	AH21	I	OV_{DD}	—
RTC	AB23	I	OV_{DD}	—
CLK_OUT	AF22	O	OV_{DD}	—

Ultimately, the final selection of an appropriate heat sink depends on many factors, such as thermal performance at a given air velocity, spatial volume, mass, attachment method, assembly, and cost. Several heat sinks offered by Aavid Thermalloy, Alpha Novatech, IERC, Chip Coolers, Millennium Electronics, and Wakefield Engineering offer different heat sink-to-ambient thermal resistances, that allows the MPC8541E to function in various environments.

16.2.1 Recommended Thermal Model

For system thermal modeling, the MPC8541E thermal model is shown in Figure 44. Five cuboids are used to represent this device. To simplify the model, the solder balls and substrate are modeled as a single block 29x29x1.6 mm with the conductivity adjusted accordingly. The die is modeled as 8.7 x 9.3 mm at a thickness of 0.75 mm. The bump/underfill layer is modeled as a collapsed resistance between the die and substrate assuming a conductivity of 4.4 W/m•K in the thickness dimension of 0.07 mm. The lid attach adhesive is also modeled as a collapsed resistance with dimensions of 8.7 x 9.3 x 0.05 mm and the conductivity of 1.07 W/m•K. The nickel plated copper lid is modeled as 11 x 11 x 1 mm.

Conductivity	Value	Unit
Lid (11 × 11 × 1 mm)		
k_x	360	W/(m × K)
k_y	360	
k_z	360	
Lid Adhesive—Collapsed resistance (8.7 × 9.3 × 0.05 mm)		
k_z	1.07	
Die (8.7 × 9.3 × 0.75 mm)		
Bump/Underfill—Collapsed resistance (8.7 × 9.3 × 0.07 mm)		
k_z	4.4	
Substrate and Solder Balls (25 × 25 × 1.6 mm)		
k_x	14.2	
k_y	14.2	
k_z	1.2	

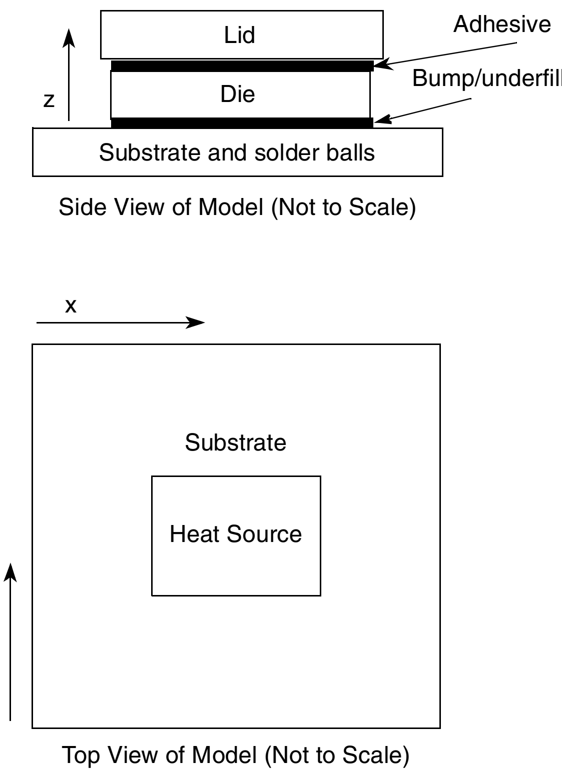


Figure 43. MPC8541E Thermal Model

the heat sink should be slowly removed. Heating the heat sink to 40–50°C with an air gun can soften the interface material and make the removal easier. The use of an adhesive for heat sink attach is not recommended.

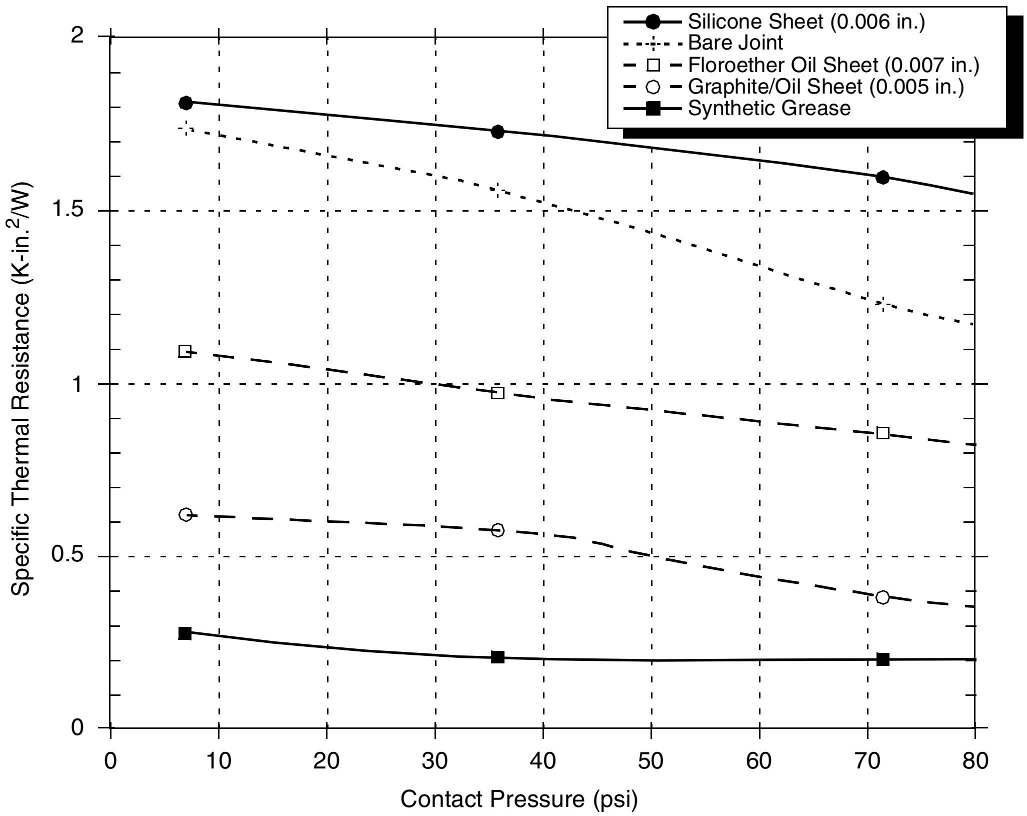


Figure 45. Thermal Performance of Select Thermal Interface Materials

The system board designer can choose between several types of thermal interface. There are several commercially-available thermal interfaces provided by the following vendors:

Chomerics, Inc. 77 Dragon Ct. Woburn, MA 01888-4014 Internet: www.chomerics.com	781-935-4850
Dow-Corning Corporation Dow-Corning Electronic Materials 2200 W. Salzburg Rd. Midland, MI 48686-0997 Internet: www.dowcorning.com	800-248-2481
Shin-Etsu MicroSi, Inc. 10028 S. 51st St. Phoenix, AZ 85044 Internet: www.microsi.com	888-642-7674
The Bergquist Company 18930 West 78th St.	800-347-4572

Chanhassen, MN 55317
Internet: www.bergquistcompany.com

Thermagon Inc. 888-246-9050
4707 Detroit Ave.
Cleveland, OH 44102
Internet: www.thermagon.com

16.2.4 Heat Sink Selection Examples

The following section provides a heat sink selection example using one of the commercially available heat sinks.

16.2.4.1 Case 1

For preliminary heat sink sizing, the die-junction temperature can be expressed as follows:

$$T_J = T_I + T_R + (\theta_{JC} + \theta_{INT} + \theta_{SA}) \times P_D$$

where

T_J is the die-junction temperature

T_I is the inlet cabinet ambient temperature

T_R is the air temperature rise within the computer cabinet

θ_{JC} is the junction-to-case thermal resistance

θ_{INT} is the adhesive or interface material thermal resistance

θ_{SA} is the heat sink base-to-ambient thermal resistance

P_D is the power dissipated by the device. See Table 4 and Table 5.

During operation the die-junction temperatures (T_J) should be maintained within the range specified in Table 2. The temperature of air cooling the component greatly depends on the ambient inlet air temperature and the air temperature rise within the electronic cabinet. An electronic cabinet inlet-air temperature (T_A) may range from 30° to 40°C. The air temperature rise within a cabinet (T_R) may be in the range of 5° to 10°C. The thermal resistance of some thermal interface material (θ_{INT}) may be about 1°C/W. For the purposes of this example, the θ_{JC} value given in Table 49 that includes the thermal grease interface and is documented in note 4 is used. If a thermal pad is used, θ_{INT} must be added.

Assuming a T_I of 30°C, a T_R of 5°C, a FC-PBGA package θ_{JC} = 0.96, and a power consumption (P_D) of 8.0 W, the following expression for T_J is obtained:

$$\text{Die-junction temperature: } T_J = 30°C + 5°C + (0.96°C/W + \theta_{SA}) \times 8.0\ W$$

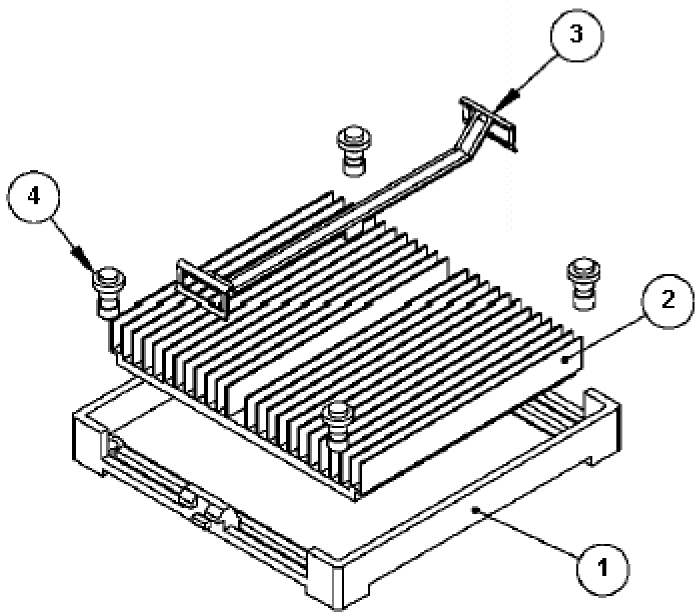
The heat sink-to-ambient thermal resistance (θ_{SA}) versus airflow velocity for a Thermalloy heat sink #2328B is shown in Figure 46.

Assuming an air velocity of 2 m/s, we have an effective θ_{SA+} of about 3.3°C/W, thus

$$T_J = 30°C + 5°C + (0.96°C/W + 3.3°C/W) \times 8.0\ W,$$

resulting in a die-junction temperature of approximately 69°C which is well within the maximum operating temperature of the component.

Item No	QTY	MEI PN	Description
1	1	MFRAME-2000	HEATSINK FRAME
2	1	MSNK-1120	EXTRUDED HEATSINK
3	1	MCLIP-1013	CLIP
4	4	MPPINS-1000	FRAME ATTACHMENT PINS



Illustrative source provided by
Millennium Electronics (MEI)

Figure 48. Exploded Views (2) of a Heat Sink Attachment using a Plastic Force

The die junction-to-ambient and the heat sink-to-ambient thermal resistances are common figure-of-merits used for comparing the thermal performance of various microelectronic packaging technologies, one should exercise caution when only using this metric in determining thermal management because no single parameter can adequately describe three-dimensional heat flow. The final die-junction operating temperature is not only a function of the component-level thermal resistance, but the system level design and its operating conditions. In addition to the component's power consumption, a number of factors affect the final operating die-junction temperature: airflow, board population (local heat flux of adjacent components), system air temperature rise, altitude, etc.

Due to the complexity and the many variations of system-level boundary conditions for today's microelectronic equipment, the combined effects of the heat transfer mechanisms (radiation convection and conduction) may vary widely. For these reasons, we recommend using conjugate heat transfer models for the boards, as well as, system-level designs.

19.2 Part Marking

Parts are marked as the example shown in Figure 53.

Notes:

MMMMM is the 5-digit mask number.
ATWLYYWWA is the traceability code.
CCCCC is the country of assembly. This space is left blank if parts are assembled in the United States.

Figure 53. Part Marking for FC-PBGA Device

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